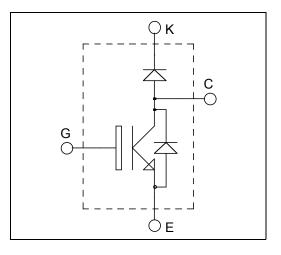


Power Matters."

ISOTOP<sup>®</sup> Boost chopper High speed Trench + Field Stop IGBT4 Power Module

# $V_{CES} = 650V$ $I_{C} = 50A$ @ Tc = 80°C





### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

#### Features

- High speed Trench + Field Stop IGBT 4
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance

#### Benefits

- Low conduction losses
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T<sub>C</sub> of V<sub>CEsat</sub>
- RoHS Compliant

All ratings (a)  $T_i = 25^{\circ}C$  unless otherwise specified

#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
I <sub>C</sub>	$T_{\rm C} = 80^{\circ}$		50	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
P <sub>D</sub>	Power Dissipation		220	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed



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## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				50	μΑ
V	Collector Emitter Saturation Voltage	$ \begin{array}{c} V_{GE} = 15V & T_{j} = 25^{\circ}C \\ I_{C} = 50A & T_{j} = 150^{\circ}C \end{array} $	$T_j = 25^{\circ}C$	1.4	1.85	2.3	V
V <sub>CE(sat)</sub>			$T_{j} = 150^{\circ}C$		2.2		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 0.8 \text{ mA}$		4.2	5.1	5.6	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				150	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			3100		
C <sub>oes</sub>	Output Capacitance				116		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz			90		
Q <sub>G</sub>	Gate charge	$V_{GE} = 15V, I_C = 50A$ $V_{CE} = 480V$			315		nC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Swite	thing (25°C)		19		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$			33		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$I_C = 50A$			197		115
T <sub>f</sub>	Fall Time	$R_G = 7\Omega$			21		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C)			19		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$			29		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 50A$			227		
T <sub>f</sub>	Fall Time	$\frac{R_{\rm C} = 50 \rm{A}}{R_{\rm G} = 7 \Omega}$			22		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$	$T_j = 150^{\circ}C$		1.2		mJ
E <sub>off</sub>	Turn off Energy	$I_{\rm C} = 50 \text{A}$ $R_{\rm G} = 7 \Omega$	$T_j = 150^{\circ}C$		1		111,0
I <sub>sc</sub>	Short Circuit data	$V_{GE} \leq 15V ; V_{Bu}$ $t_p \leq 5\mu s ; T_j = 15$			350		А
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.68	°C/W

## Chopper diode ratings and characteristics

Symbol	Characteristic	<b>Test Conditions</b>		Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage					650	V
I <sub>RM</sub>	Reverse Leakage Current	$V_R = 650V$				50	μA
I <sub>F</sub>	DC Forward Current		$Tc = 25^{\circ}C$		50		Α
V <sub>F</sub>	Diode Forward Voltage	$I_F = 50A$	$T_i = 25^{\circ}C$		1.6	2	v
۷F	Diode i of ward Voltage	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		•
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
۲r	Reverse Recovery Time	1 504	$T_{j} = 150^{\circ}C$		150		115
Q <sub>rr</sub>	Reverse Recovery Charge	$I_F = 50A$ $V_R = 300V$ $di/dt = 1800A/\mu s$	$T_j = 25^{\circ}C$		2.6		μC
Qrr	Reverse Recovery charge		$T_{j} = 150^{\circ}C$		5.4		μΟ
E <sub>rr</sub>			$T_j = 25^{\circ}C$		0.6		mJ
LIL	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		1.2		1115
R <sub>thJC</sub>	Junction to Case Thermal Resistance					1.14	°C/W

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2 - 6



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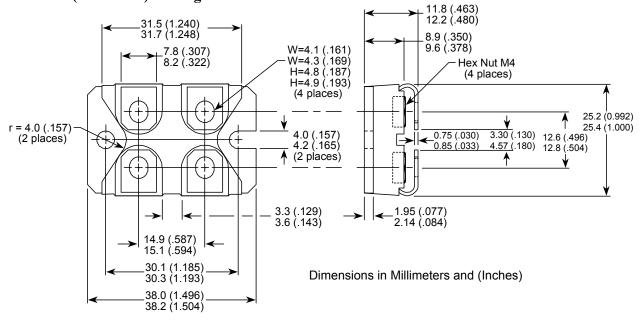
### IGBT parallel diode ratings and characteristics

-	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage					650	V
I <sub>RM</sub>	Reverse Leakage Current	$V_R = 650V$				50	μA
$I_{\rm F}$	DC Forward Current		$Tc = 60^{\circ}C$		20		А
V <sub>F</sub>	Diode Forward Voltage	$I_{\rm F} = 20A$ $V_{\rm GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
· 1			$T_{j} = 150^{\circ}C$		1.5		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
۹r	Reverse Receivery Time	x 20.4	$T_{j} = 150^{\circ}C$		150		115
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{\rm R} = 300 V$	$T_j = 25^{\circ}C$		1.1		μC
Qrr	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		2.3		μĊ
Err	Reverse Recovery Energy		$T_j = 25^{\circ}C$		0.23		mJ
			$T_{j} = 150^{\circ}C$		0.50		1115
R <sub>thJC</sub>	Junction to Case Thermal Resistance					2.6	°C/W

### Thermal and package characteristics

Symbol	Characteristic	Min	Тур	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz	2500			V
$T_J, T_{STG}$	Storage Temperature Range	-55		175	
$T_{\text{JOP}}$	Recommended junction temperature under switching conditions	-55		T <sub>J</sub> max -25	°C
T <sub>L</sub>	Max Lead Temp for Soldering:0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

## SOT-227 (ISOTOP<sup>®</sup>) Package Outline



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3 - 6



**Output Characteristics** 

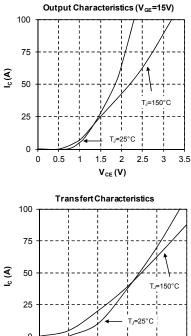
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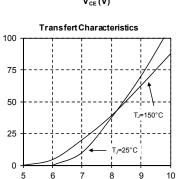
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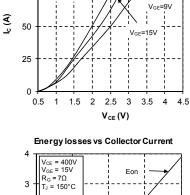
T<sub>J</sub> = 150°C

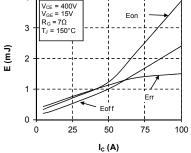
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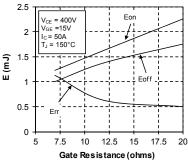




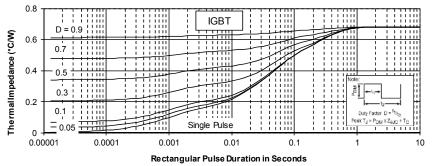


Switching EnergyLosses vs Gate Resistance

 $V_{GE}(V)$ 

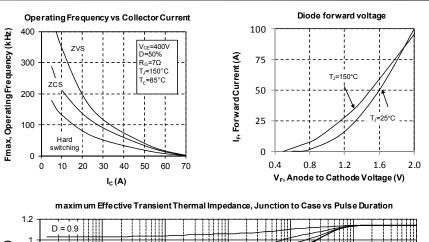


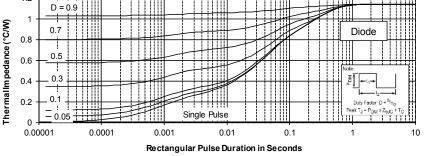
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



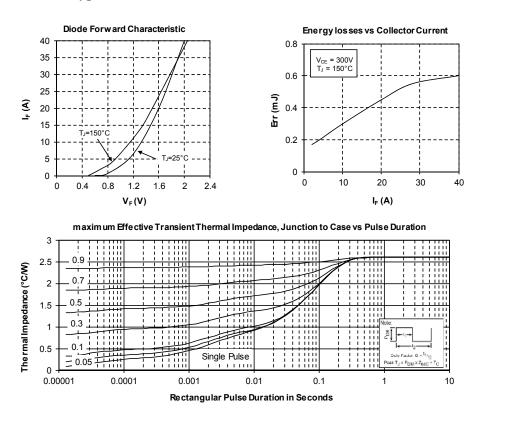
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### **IGBT** parallel diode Typical Performance Curves



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